

3. The method of claim 2, further comprising, subsequent to removing the second relief pattern and the first relief pattern, removing uncovered portions of the conformal film such that top surfaces of the first metal lines are uncovered.
4. The method of claim 1, wherein the first dielectric lines, the second dielectric lines, and the dielectric layer is comprised of a same material.
5. The method of claim 1, wherein forming the first relief pattern includes forming the first relief pattern in a hardmask layer deposited above the dielectric layer.
6. The method of claim 1, wherein forming the second relief pattern above the dielectric layer includes forming the second relief pattern above the first relief pattern.
7. The method of claim 1, wherein forming the second relief pattern above the dielectric layer includes forming the second relief pattern in plane with the first relief pattern.
8. The method of claim 7, wherein forming the second relief pattern in plane with the first relief pattern includes executing a freeze operation that prevents subsequent solubility changes of the first relief pattern.
9. The method of claim 2, wherein the predetermined metal is copper.
10. The method of claim 2, wherein metallizing the dielectric layer includes removing an overburden of the predetermined metal above a top surface of the dielectric layer.